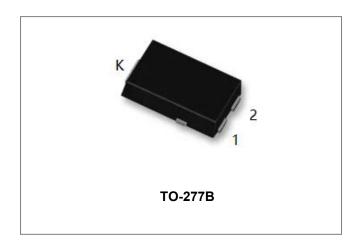




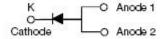
### ST8100S SCHOTTKY RECTIFIER



#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Trench MOS Schottky technology
- "-A" is an AEC-Q101 qualified device
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- · Reverse battery protection

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T∟=125°C, rectangular wave form	8	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>J</sub> = 25 °C	150	Α

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 4A, Pulse, T <sub>J</sub> = 25 °C @ 8A, Pulse, T <sub>J</sub> = 25 °C	0.52 0.66	- 0.68	V
	$V_{F2}$	@ 4A, Pulse, T <sub>J</sub> = 125 °C @ 8A, Pulse, T <sub>J</sub> = 125 °C	0.47 0.58	- 0.62	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	13.5	70	uA
Reverse Current*	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125  ^{\circ}\text{C}$	3.5	15	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz$	542	-	pF

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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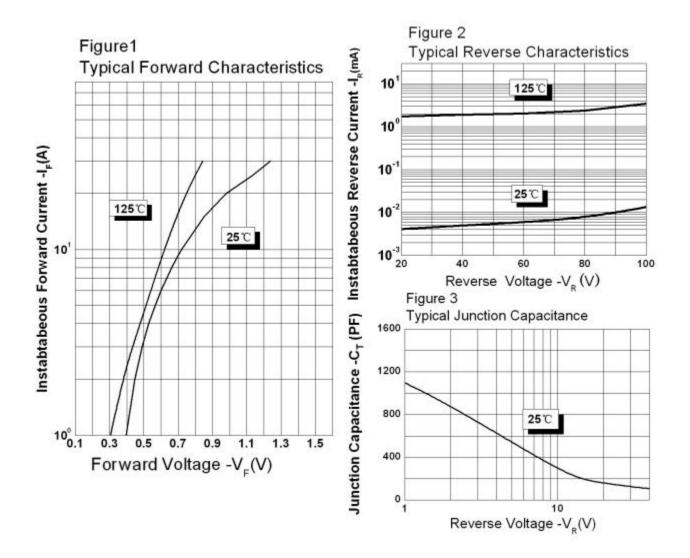




### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	$T_{stg}$	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	-	3.5	°C/W
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$		70	°C/W
Approximate Weight	wt	-	0.08	g

# **Ratings and Characteristics Curves**

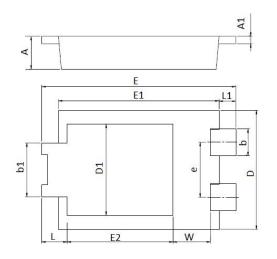


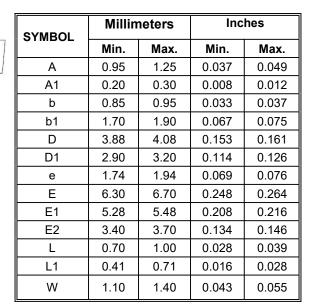
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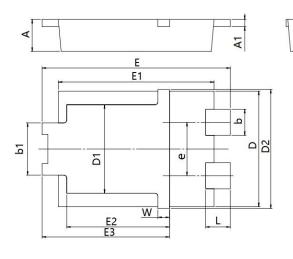


#### **Mechanical Dimensions TO-277B**





#### **Mechanical Dimensions TO-277B(New)**



SYMBOL	Millimeters		Inches		
STIVIBUL	Min.	Max.	Min.	Max.	
Α	0.95	1.25	0.037	0.049	
A1	0.20	0.30	0.008	0.012	
b	0.85	0.95	0.033	0.037	
b1	1.70	1.90	0.067	0.075	
D	3.88	4.08	0.153	0.161	
D1	2.90	3.20	0.114	0.126	
D2	4.25	-	0.167	-	
е	1.74	1.94	0.069	0.076	
E	6.30	6.70	0.248	0.264	
E1	5.28	5.48	0.208	0.216	
E2	3.40	3.70	0.134	0.146	
E3	4.20	4.60	0.165	0.181	
L	0.65	1.05	0.025	0.041	
W	0.25	0.55	0.010	0.022	

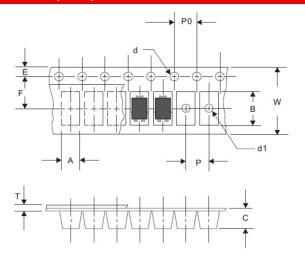
Notes: New Mechanical Dimensions is performed from date code 2236X.

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#### **Carrier Tape Specification TO-277B**



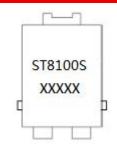
SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	4.28	4.48	
В	6.80	7.10	
С	1.30	1.50	
d	1.40	1.60	
d1	-	1.50	
E	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
Т	0.24	0.44	
W	11.70	12.30	

#### **Ordering Information**

Device	Package	Shipping
ST8100S	TO-277B(Pb-Free)	5000pcs/ reel
ST8100STR	TO-277B(Pb-Free)	5000pcs/ reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

#### **Marking Diagram**



Where XXXXX is YYWWL

 ST
 = Device Type

 8
 = Forward Current (8A)

 100
 = Reverse Voltage (100V)

 S
 = Package type

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

#### DISCLAIMER:

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